1 2 4972251.pn. 2 4972251.pn. 3 528 (438/108).CCLS. 2 528 (438/108).CCLS. 3 3 (438/108).CCLS.) and protective with film with surface with (chip IC die semiconductor) 4 801 (438/s).ccls. and protective with film with surface with (chip IC die semiconductor) 5 34 (438/s).ccls. and protective with film with surface with (chip IC die semiconductor) 5 4 801 (438/s).ccls. and protective with film with surface with (chip IC die semiconductor) 6 1256 (257/692).CCLS.) and protective with film with surface with (chip IC die semiconductor) 6 1256 (257/692).CCLS.) and passivation and flip SPO, JPO, DERMENT, IBM TOB USPAT, US-POPUB, EPO, JPO, DERMENT, IBM TOB USPAT, U	L Number	Hits	Search Text	DB	Time stamp
2 528 (438/109).CCLS. DERWENT; IEM TOB USPAT; US-PCPUB; EPO, JPO; DERWENT; US-PCPUB; EPO; JPO; DERWENT; EPO; JPO; JPO; DERWENT; EPO; JPO; JPO; DERWENT; EPO; JPO; JPO; JPO; JPO; JP	1	2	4972251.pn.		2002/08/20 10:31
Second S		500	/420/100\ COTO	DERWENT; IBM_TDB	0000 (00 (00 10 01
### with surface with (chip IC die semiconductor) 4	2	528	(438/108).CCLS.	US-PGPUB; EPO; JPO; DERWENT;	2002/08/20 10:31
Sol	3	3	with surface with (chip IC die	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/08/20 10:33
34	4	801	with surface with (chip IC die	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/08/20 10:34
6	5	34	with surface with (chip IC die	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/08/20 11:29
S-PGPUB; EPO; JPO; DERWENT; IBM TDB	6	1256	(257/692).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/08/20 11:29
8 41 ((257/692).CCLS.) and passivation USPĀT; US-PGPUB; EPG; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPG; JPO; DERWENT; ISM_TDB USPĀT; US-PGPUB; EPG; JPO; DERWENT; US-PGPUB; EPG; J	7	14	((257/692).CCLS.) and passivation and flip	US-PGPUB; EPO; JPO; DERWENT;	2002/08/20 11:30
9 193 ((257/692).CCLS.) and insulating with layer USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; DERWE	8	41	((257/692).CCLS.) and passivation	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/08/20 11:30
10 667 (257/\$).ccls. and passivation and flip USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	9	193		USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/08/20 11:30
11	10	667	(257/\$).ccls. and passivation and flip	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/08/20 11:31
- 2682 Continuation with PCT - 18 (Continuation with PCT) and Continuation with PCT and (257/\$).ccls. - 2 5470787.pn. Continuation with PCT) and Continuation with PCT and (257/\$).ccls. 2 5470787.pn. USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	11	249		USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/08/20 11:31
- 18 (Continuation with PCT) and Continuation USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	_	2682	Continuation with PCT	USPAT; US-PGPUB; EPO; JPO; DERWENT;	
- 2 5470787.pn. USPĀT; 2002/08/19 14:55 US-PGPUB; EPO; JPO; DERWENT;	_	18	1 '	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/08/19 12:16
	_	2	5470787.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/08/19 14:55

Page 1

-	472	(passivation with lay	er with made)	and	USPAT;	2
		(438/\$).ccls.			US-PGPUB;	
					EPO; JPO;	

			1	
-	472	(passivation with layer with made) and (438/\$).ccls.	USPAT; US-PGPUB;	2002/08/19 14:57
		(100)	EPO; JPO;	
	;		DERWENT;	
			IBM TDB	
_	50	((passivation with layer with made) and	USPAT;	2002/08/19 15:07
		(438/\$).ccls.) and solder with bump	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	40	5736456.URPN.	USPAT	2002/08/19 14:59
_	521	passivation with layer with (silicon adj	USPAT;	2002/08/19 15:14
		nitride silicon oxide MgO) and bump	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	222	(passivation with layer with (silicon adj	USPĀT;	2002/08/19 15:15
		nitride silicon oxide MgO) and bump) and	US-PGPUB;	
		(257/\$).ccls.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	252	passivation with layer with (silicon adj	USPĀT;	2002/08/19 15:15
		nitride silicon adj oxide MgO) and bump	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
1			IBM TDB	
-	109	(passivation with layer with (silicon adj	USPĀT;	2002/08/19 15:25
•		nitride silicon adj oxide MgO) and bump)	US-PGPUB;	•
		and (257/\$).ccls.	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	5	("4434434" "5268072" "5629564"	USPAT	2002/08/19 15:21
		"5785236" "5795819").PN.		
_	90	passivation with layer with thermal with	USPAT;	2002/08/19 15:44
		expansion	US-PGPUB;	
		*	EPO; JPO;	
			DERWENT;	
			IBM TDB	
i –	22218	silicon with germanium dioxide with	USPAT;	2002/08/19 15:52
		layer with thermal with coefficient	US-PGPUB;	
i			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	151	(silicon with germanium dioxide with	USPAT;	2002/08/19 15:50
		layer with thermal with coefficient) and	US-PGPUB;	
		passivation with layer and bump	EPO; JPO;	
1			DERWENT;	
1			IBM_TDB	
-	3	silicon with germanium with dioxide with	USPĀT;	2002/08/19 15:53
		layer with thermal with coefficient	US-PGPUB;	
	1		EPO; JPO;	
			DERWENT;	
	[IBM_TDB	
-	479795	silicon with dioxide with coefficient	USPĀT;	2002/08/19 15:57
[1	with thermal expansion	US-PGPUB;	
	İ		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	9020	(silicon with dioxide with coefficient	USPAT;	2002/08/19 15:58
	[with thermal expansion) and (257/\$).ccls.	US-PGPUB;	
İ			EPO; JPO;	
1			DERWENT;	
1	1		IBM_TDB	
-	1751	((silicon with dioxide with coefficient	USPAT;	2002/08/19 15:56
1	[with thermal expansion) and	US-PGPUB;	
	1	(257/\$).ccls.) and bump	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
				

_	325	(((silicon with dioxide with	USPAT;	2002/08/19 15:56
		coefficient with thermal expansion) and	US-PGPUB;	
		(257/\$).ccls.) and bump) and passivation	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	243	(((silicon with dioxide with	USPAT;	2002/08/19 15:56
		coefficient with thermal expansion) and	EPO; JPO;	
		(257/\$).ccls.) and bump) and passivation	DERWENT;	
			IBM TDB	
_	277	silicon with dioxide with coefficient	USPAT;	2002/08/19 16:03
		with thermal with expansion	EPO; JPO;	
		•	DERWENT;	
			IBM TDB	
_	72	(silicon with dioxide with coefficient	USPAT;	2002/08/19 16:00
		with thermal with expansion) and	US-PGPUB;	
		(257/\$).ccls.	EPO; JPO;	
			DERWENT;	
_			IBM TDB	
_	0	silicon adj dioxide with "coefficient of	USPAT;	2002/08/19 16:04
		thermal expansion"	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	116	silicon adj dioxide with "thermal	USPAT;	2002/08/19 16:13
		expansion coefficient"	EPO; JPO;	
		*	DERWENT;	
			IBM TDB	
_	20673	silicon with germanium dioxide with	USPAT;	2002/08/19 16:14
		"thermal expansion coefficient"	EPO; JPO;	
		•	DERWENT;	
			IBM TDB	
_	3	silicon with germanium with dioxide with	USPĀT;	2002/08/19 16:21
!		"thermal expansion coefficient"	EPO; JPO;	
		-	DERWENT;	
			IBM_TDB	
-	7	,	USPĀT;	2002/08/19 16:27
		"thermal expansion"	EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	
-	4		USPAT;	2002/08/19 16:22
		"thermal expansion") not (silicon with	EPO; JPO;	
		germanium with dioxide with "thermal	DERWENT;	
		expansion coefficient")	IBM_TDB	
-	9		USPAT;	2002/08/20 09:42
	1	"thermal expansion"	EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
-	1	,	US-PGPUB	2002/08/19 16:31
		"thermal expansion"		